TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

# 2SC4213

## For Muting and Switching Applications

Unit: mm

• High emitter-base voltage:  $V_{EBO} = 25 \text{ V (min)}$ 

• High reverse hFE: Reverse hFE = 150 (typ.) ( $V_{CE} = -2 \text{ V}$ ,  $I_{C} = -4 \text{ mA}$ )

• Low on resistance:  $R_{ON} = 1 \Omega$  (typ.) ( $I_B = 5 \text{ mA}$ )

• High DC current gain: hFE = 200~1200

• Small package

#### **Absolute Maximum Ratings (Ta = 25°C)**

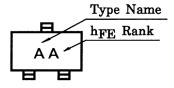
Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	50	V
Collector-emitter voltage	V <sub>CEO</sub>	20	V
Emitter-base voltage	V <sub>EBO</sub>	25	V
Collector current	IC	300	mA
Base current	ΙΒ	60	mA
Collector power dissipation	PC	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T <sub>stg</sub>	-55~125	°C

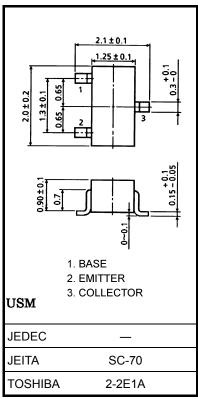
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e.

operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

# Marking





Weight: 0.006 g (typ.)

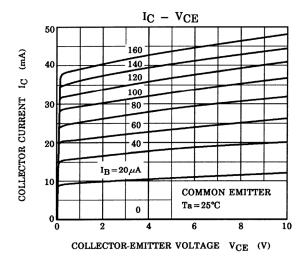


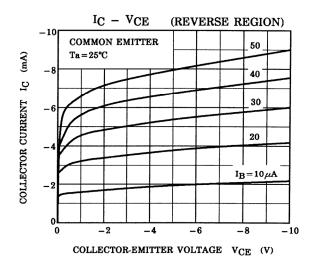
# **Electrical Characteristics (Ta = 25°C)**

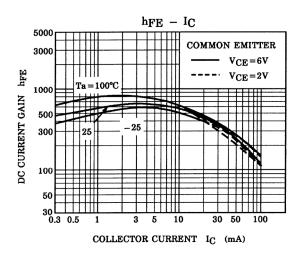
Chara	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off cu	urrent	I <sub>CBO</sub>	$V_{CB} = 50 \text{ V}, I_E = 0$	_	_	0.1	μΑ
Emitter cut-off cur	rent	I <sub>EBO</sub>	V <sub>EB</sub> = 25 V, I <sub>C</sub> = 0	_	_	0.1	μΑ
DC current gain		h <sub>FE</sub> (Note)	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 4 mA	200	_	1200	
Collector-emitter s	saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = 30 A, I <sub>B</sub> = 3 mA	_	0.042	0.1	V
Base-emitter volta	ge	V <sub>BE</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 4 mA	_	0.61	_	V
Transition frequen	icy	f <sub>T</sub>	V <sub>CE</sub> = 6 V, I <sub>C</sub> = 4 mA	_	30	_	MHz
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	_	4.8	7	pF
Switching time Storage	Turn-on time	t <sub>on</sub>	OUTPUT $10V = 1 \mu s$ $V_{BB} V_{CC}$ $= -3V = 12V$ Duty cycle $\leq 2\%$	_	160	_	
	Storage time	t <sub>stg</sub>		_	500	_	ns
	Fall time	t <sub>f</sub>		_	130	_	

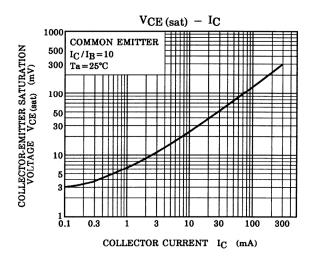
Note: hFE classification A: 200~700, B: 350~1200

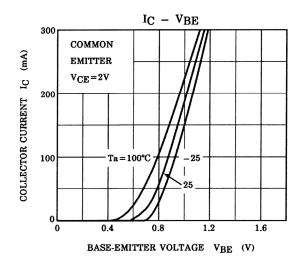
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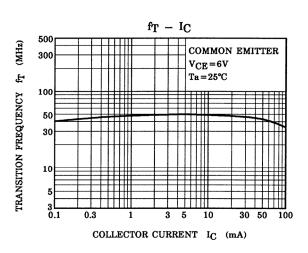




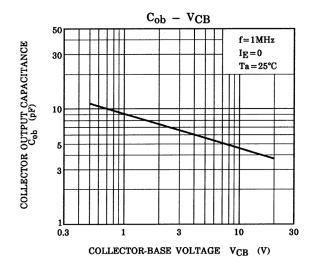


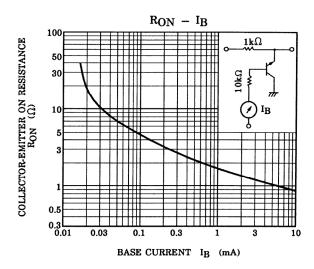


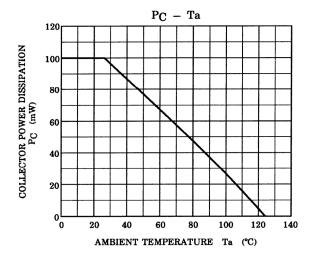




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20070701-EN GENERAL

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